## Erratum

# Electrical characteristics and photodetection mechanism of $TiO_2$/AlGaN/GaN heterostructure-based ultraviolet detectors with a Schottky junction (J. Mater. Chem. C (2023) 11 (1704–1713) DOI: 10.1039/D2TC04491A)

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CORRECTION





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# Correction: Electrical characteristics and photodetection mechanism of $TiO_2$/AlGaN/GaN heterostructure-based ultraviolet detectors with a Schottky junction

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Correction for 'Electrical characteristics and photodetection mechanism of $TiO_2$/AlGaN/GaN heterostructure-based ultraviolet detectors with a Schottky junction' by Teng Zhan *et al.*, *J. Mater. Chem. C*, 2023, **11**, 1704–1713, https://doi.org/10.1039/D2TC04491A.

The authors regret an error in the abstract of the published article: the text "(i) the Schottky emission mechanism at a low reverse voltage (0–1 V) before the current is fully turned on." should be changed to "(i) the Schottky emission mechanism at a low reverse voltage (0 to −1 V) before the current is fully turned on." This change does not affect the main conclusions of the manuscript. The authors would like to apologize for any inconvenience caused.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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